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INFORMATION DISCLOSURE STATEMENT BY APPLICANT				**Application Number**	10/582,392
				Filing Date	June 28, 2007
				First Named Inventor	Horsky et al.
(use as many sheets as necessary)				**Group Art Unit**	2821
				Examiner Name	Bernard Souw
Sheet	1	of	1	**Attorney Docket Number**	211843-00044

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OTHER PRIOR ART – NON PATENT LITERATURE DOCUMENTS

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	C1	E.J. Collart et al. "Co-Implantation with Conventional Spike Anneal Solutions for 45 nm Ultra-Shallow Junction Formation", Proceedings of the Eight International Workshop on: Fabrication, Characterization and Modeling Of Ultra-Shallow Doping Profiles in Semiconductors, June 2005, p. 327	
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Examiner Signature	/Bernard Souw/		05/26/2010

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